TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSVII-H)

# **TK150E09NE**

#### ■ E-Bike

• Low drain-source ON resistance :  $RDS(ON) = 3.6 \text{ m}\Omega \text{ (typ.)} \text{ (VGS} = 10 \text{ V)}$ 

• Low leakage current :  $IDSS = 10 \mu A (max) (VDS = 85 V)$ 

• Enhancement mode :  $V_{th} = 2.5 \sim 4.5 \text{ V (V}_{DS} = 10 \text{ V}, I_{D} = 1.0 \text{ mA})$ 

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	85	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Tc = 25°C) (Note 1)	I <sub>D</sub>	150		
	DC (Tc = 100°C) (Note 1)	I <sub>D</sub>	120	Α	
	Pulse (Note 1)	I <sub>DP</sub>	450		
Drain power dissipation (Tc = 25°C)		$P_{D}$	230	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	161	mJ	
Avalanche current (Note 2)		I <sub>AS</sub>	72	Α	
Peak diode recovery dv/dt (Note 5)		dv/dt	12	V/ns	
Channel temperature		T <sub>ch</sub>	175	°C	
Storage temperature range		T <sub>stg</sub>	<b>−</b> 55~175		

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	0.65	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	83.3		

Note 1: Ensure that the channel temperature does not exceed 175°C.

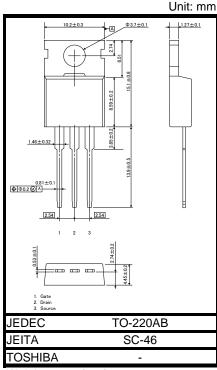
Note 2:  $V_{DD}$  = 64 V,  $T_{ch}$  = 25°C (initial), L =24  $\mu H,~R_{G}$  = 25  $\Omega,~I_{AS}$  = 72A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

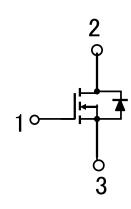
Note 4: I<sub>DR</sub>≤180A,di/dt≤160A/µs, Tch≤Tch max.

This transistor is an electrostatic-sensitive device.

Please handle with caution.



Weight: 1.9 g (typ.)



Note :Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc). Thermal Characteristics

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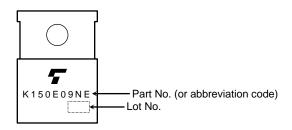
# Electrical Characteristics (Ta = 25°C)

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	_	_	±0.1	
Drain cut-off cu	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 85 V, V <sub>DS</sub> = 0 V	_	_	10	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	85	_	_	
Drain-source breakdown voltage		V (BR) DSX	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	60	_	_	V
Gate threshold v	oltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	2.5	_	4.5	
Drain-source O	N resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A	_	3.65	5.0	mΩ
Input capacitano	e	C <sub>iss</sub>			5500		
		C <sub>rss</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	38	_	pF
		Coss		_	1300	_	
Switching time	Rise time	t <sub>r</sub>	10 V	_	19	_	ns
	Turn-on time	t <sub>on</sub>		_	42	_	
	Fall time	t <sub>f</sub>		l	28	ı	
	Turn-off time	t <sub>off</sub>	$V_{DD} \simeq 40 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \text{ μs}$		93		
Total gate charge (Gate-source plus gate-drain)		Qg		ı	81	1	
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD} \approx 64 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 72 \text{ A}$		29	_	nC
Gate-drain charge		Q <sub>gd</sub>			21	_	
Gate switch charge		$Q_{\text{SW}}$			33		

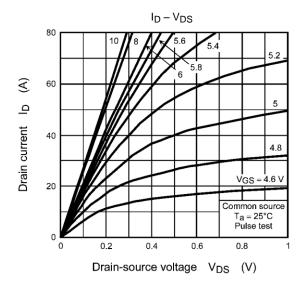
# Source-Drain Ratings and Characteristics (Ta = 25°C)

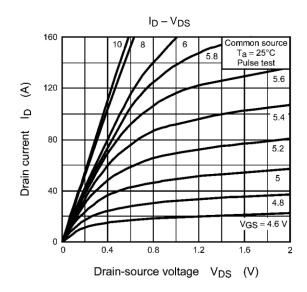
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Tc = 25°C) (Note 1)	I <sub>DR</sub>	_	_	_	150	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	450	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 150 A, V <sub>GS</sub> = 0 V	_	_	-1.3	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 72 A, V <sub>GS</sub> = 0 V		77	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> / dt = 100 A / μs		150	_	nC

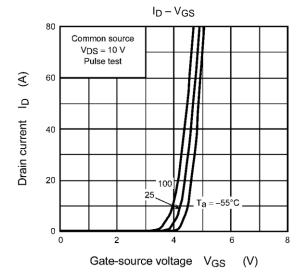
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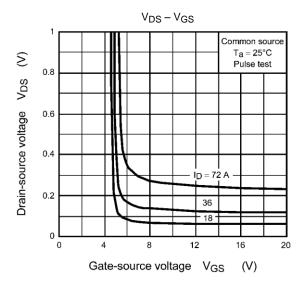


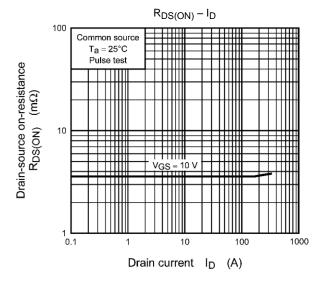
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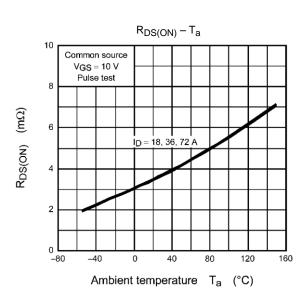


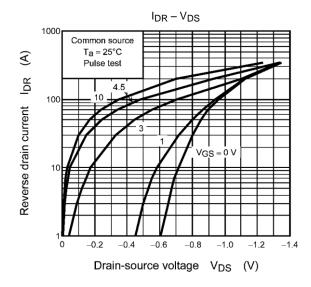


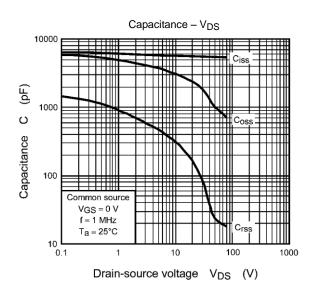


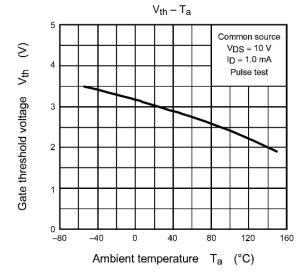


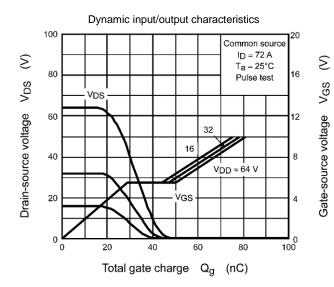


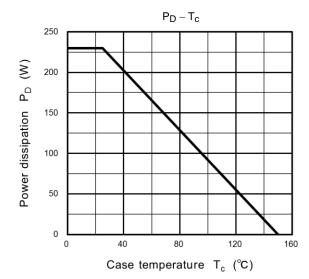




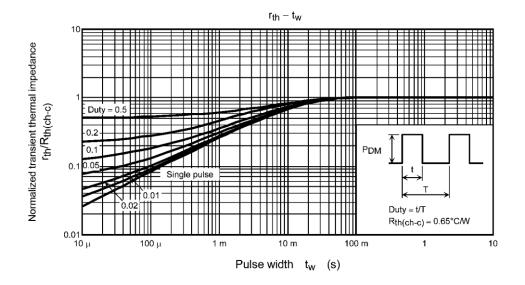


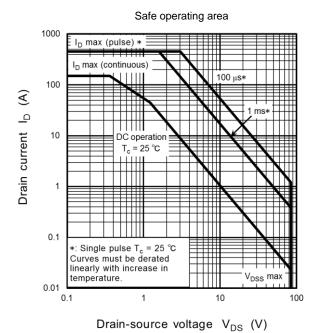


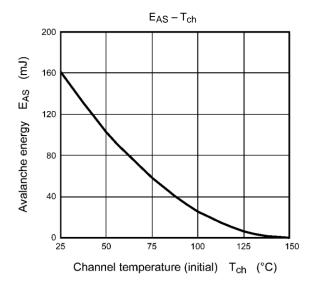


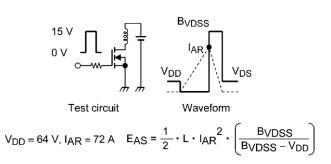


4









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6